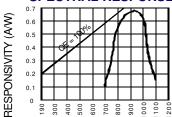


PARAMETER	MIN	MAX	UNITS
Reverse Voltage		100	V
Storage Temperature	-55	+100	°C
Operating Temperature Range	-40	+80	°C
Soldering Temperature*		+240	°C
Light Current		1.0	mA
	Reverse Voltage Storage Temperature Operating Temperature Range Soldering Temperature*	Reverse Voltage -55 Storage Temperature -40 Soldering Temperature* -	Reverse Voltage100Storage Temperature-55Operating Temperature Range-40Soldering Temperature*+240



WAVELENGTH (nm)

1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current	H = 100 fc, 2850 K	40	59		mA
ΙD	Dark Current	$H = 0, V_{_{\rm R}} = 10 \text{ V}$		1.0	5.0	nA
RsH	Shunt Resistance	$H = 0, V_{_{\rm R}} = 10 \text{ mV}$.5	2		GΩ
TC Rsh	RSH Temp. Coefficient	$H = 0, V_{_{\rm R}} = 10 \text{ mV}$		-8		% / °C
CJ	Junction Capacitance	$H = 0, V_{_{\rm R}} = 10 V^{**}$		15		pF
λrange	Spectral Application Range	Spot Scan	700		1100	nm
λρ	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	l = 10 m A	100	125		V
N EP	Noise Equivalent Power	VR = 10 V @ Peak		2.5x10 ⁻¹⁴		W/ / Hz
tr	Response Time	$RL = 1 K\Omega V_{R} = 50 V$		15		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1 MHz